



FINAL PRODUCT/PROCESS CHANGE NOTIFICATION #16772

Generic Copy

16-Dec-2011

TITLE: Final Notification for Transfer of CCR (Constant Current Regulator) Devices from ON Semiconductor Aizu, Japan wafer fab to ON Semiconductor Roznov, Czech Republic wafer fab CZ4

PROPOSED FIRST SHIP DATE: 16-Mar-2012

AFFECTED CHANGE CATEGORY(S): ON Semiconductor Fab Site

FOR ANY QUESTIONS CONCERNING THIS NOTIFICATION:

Contact your local ON Semiconductor Sales Office or David Helzer <david.helzer@onsemi.com>

SAMPLES: Contact your local ON Semiconductor Sales Office

ADDITIONAL RELIABILITY DATA: Available. Contact your local ON Semiconductor Sales Office or Donna Scheuch <Donna.Scheuch@onsemi.com>

NOTIFICATION TYPE:

Final Product/Process Change Notification (FPCN)

Final change notification sent to customers. FPCNs are issued at least 90 days prior to implementation of the change.

ON Semiconductor will consider this change approved unless specific conditions of acceptance are provided in writing within 30 days of receipt of this notice. To do so, contact <quality@onsemi.com>.

DESCRIPTION AND PURPOSE:

ON Semiconductor announced in October 2011 its plan to close the Aizu, Japan facility in 2012 to realize operational efficiencies (reference Press Release <http://www.onsemi.com/PowerSolutions/newsItem.do?article=2618>).

ON Semiconductor has qualified the Roznov, Czech Republic CZ4 wafer facility to manufacture CCR wafers and is notifying customers regarding wafer fabrication for the "List of affected General Parts". This list of devices has been qualified to be transferred from ON Semiconductor Aizu, Japan to ON Semiconductor's CZ4 wafer fabrication facility in Roznov, Czech Republic. The CZ4 facility has been manufacturing and shipping wafers for other devices from this family since August 2011.

Upon expiration of the associated Final PCN, devices may be supplied from either the Aizu or CZ4 wafer fab.

Due to equipment differences between the two wafer manufacturing facilities, minor mask changes were required to achieve the same product electrical parameters. No changes to product parameters or packaging occurred as a result of this wafer fab qualification.



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RELIABILITY DATA SUMMARY:

Qual Vehicle: NSI45030AT1G (package: SOD-123)
 Reliability Test Results of NSI45030AT1G:

Test	Test Conditions	Interval	Sample Size	Results
HTOL	T _j = 150°C for 1008 hours	1008 hrs	3 lots x 80 units/lot	0/240
HTSL	T _a = 150°C for 1008 hours	1008 hrs	3 lots x 80 units/lot	0/240
AC+PC	Temp= +130°C, 15psi, RH=100%	96 hrs	3 lots x 80 units/lot	0/240
TC+PC	T _a = -65 to +150C	1000 cyc	3 lots x 80 units/lot	0/240

Qual Vehicle: NSI45090JDT4G (package: DPAK)
 Reliability Test Results of NSI45090JDT4G:

Test	Test Conditions	Interval	Sample Size	Results
HTOL	T _j = 150°C for 1008 hours	1008 hrs	3 lots x 80 units/lot	0/240
HTSL	T _a = 150°C for 1008 hours	1008 hrs	3 lots x 80 units/lot	0/240
AC+PC	Temp= +130°C, 15psi, RH=100%	96 hrs	3 lots x 80 units/lot	0/240
TC+PC	T _a = -65 to +150C	1000 cyc	3 lots x 80 units/lot	0/240

CHANGED PART IDENTIFICATION:

Affected products from ON Semiconductor with date code marking starting WW12 (2012) and greater may be sourced from either the Aizu Wafer Fab in Japan or the CZ4 Wafer fab in Roznov, Czech Republic.

ELECTRICAL CHARACTERISTIC SUMMARY:

Available upon request

List of affected General Parts:

- NSI45030AT1G
- NSI45030T1G
- NSI45025AT1G
- NSI45025T1G
- NSI45020AT1G
- NSI45020T1G
- NSI45015WT1G
- NSI50010YT1G
- NSI45030AZT1G
- NSI45030ZT1G
- NSI45025AZT1G
- NSI45025ZT1G
- NSI45090JDT4G
- NSI45060JDT4G
- NSI45035JZT1G
- NSI45020JZT1G